

μPA502CT

N-CHANNEL MOSFET FOR SWITCHING

R07DS1277EJ0200 Rev.2.00 Jul 06, 2015

Description

The μ PA502CT, N-channel vertical type MOSFET designed for general-purpose switch, is a device which can be driven directly by a 4.5 V power source.

Features

- Two MOSFET circuits (Two source common)
- Directly driven by a 4.5 V power source.
- Low on-state resistance

 $R_{DS(on)1} = 2.7 \Omega MAX. (V_{GS} = 10 V, I_{D} = 100 mA)$

 $R_{DS(on)2} = 3.2 \Omega MAX. (V_{GS} = 4.5 V, I_{D} = 50 mA)$

Ordering Information

Part Number	Lead Plating	Packing	Package	
μPA502CT-T1-A/AT	-A : Sn-Bi , -AT : Pure Sn	3000p/Reel	SC-74A (5pMM)	

Remark "-A/AT" indicates Pb-free. This product does not contain Pb in external electrode and other parts.

Marking UE

Absolute Maximum Ratings (TA = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	VDSS	60	V
Gate to Source Voltage (V _{DS} = 0 V)	Vgss	±20	V
Drain Current (DC)	I _{D(DC)}	±100	mA
Drain Current (pulse) Note	ID(pulse)	±200	mA
Total Power Dissipation	Рт	300 (Total)	mW
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

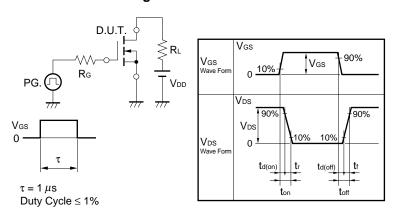
Note PW \leq 10 μ s, Duty Cycle \leq 1%

Electrical Characteristics (T_A = 25°C)

Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Ipss	V _{DS} = 60 V, V _{GS} = 0 V			1	μА
Gate Leakage Current	Igss	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±10	μА
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		2.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 100 mA	150			mS
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 10 V, I _D = 100 mA		2.1	2.7	Ω
	RDS(on)2	V _{GS} = 4.5 V, I _D = 50 mA		2.4	3.2	Ω
Input Capacitance	Ciss	V _{DS} = 10 V,		20		pF
Output Capacitance	Coss	V _{GS} = 0 V,		9		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		2		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 10 V,		16		ns
Rise Time	tr	I _D = 200 mA,		6.5		ns
Turn-off Delay Time	t _{d(off)}	V _{GS} = 10 V,		82		ns
Fall Time	tf	R _G = 10 Ω		32		ns
Total Gate Charge	Q _G	I _D = 200 mA, V _{DD} = 25 V, V _{GS} = 10 V		2		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 200 mA, V _{GS} = 0 V		0.86		V

Note Pulsed

Test Circuit Switching Time

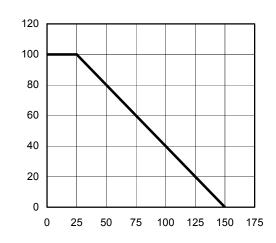


dT - Percentage of Rated Power - %

Ib - Drain Current - mA

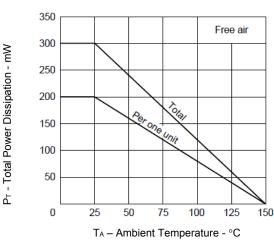
Typical Characteristics (T_A = 25°C)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

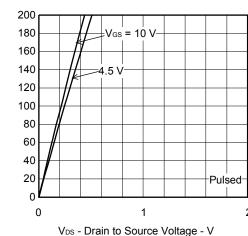


T_A – Ambient Temperature - °C

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE

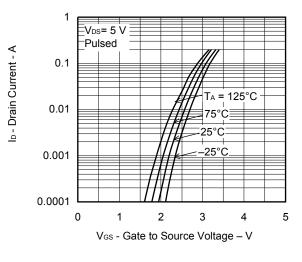


DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

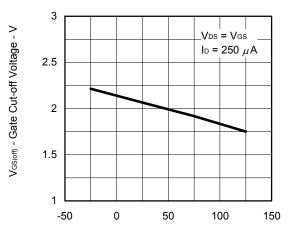


VBS - Drain to Cource Voltage - V

FORWARD TRANSFER CHARACTERISTICS

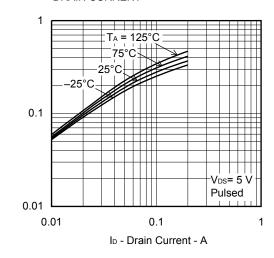


GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



 T_{ch} - Channel Temperature - $^{\circ}C$

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



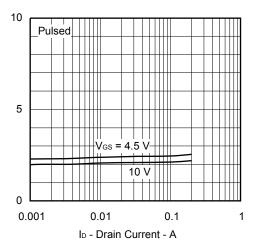
| yfs | - Forward Transfer Admittance -

 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - Drain to Source On-state Resistance - Ω

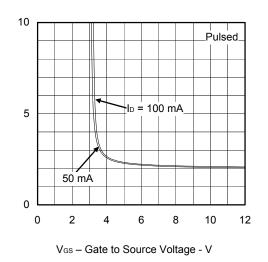
 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - Drain to Source On-state Resistance - Ω

ta(on), tr, ta(off), tr - Switching Time - ns

DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**

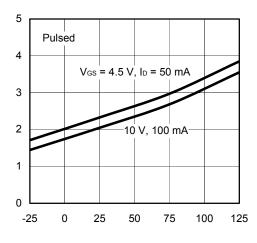


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

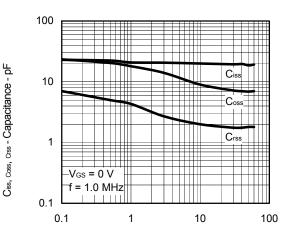


 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - Drain to Source On-state Resistance - Ω

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



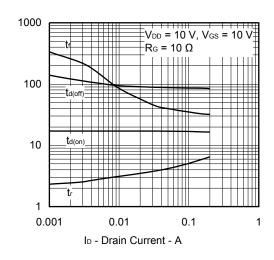
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



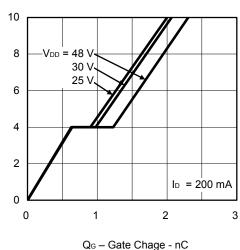
Tch - Channel Temperature - °C

 $V_{\text{\scriptsize DS}}$ - Drain to Source Voltage – V

SWITCHING CHARACTERISTICS



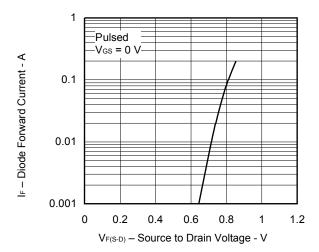
DYNAMIC INPUT CHARACTERISTICS

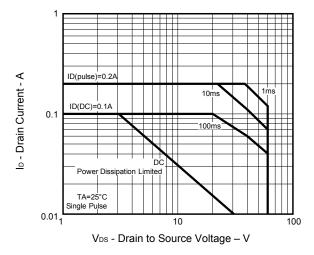


Ves - Gate to Source Voltage - V

SOURCE TO DRAIN DIODE FORWARD VOLTAGE

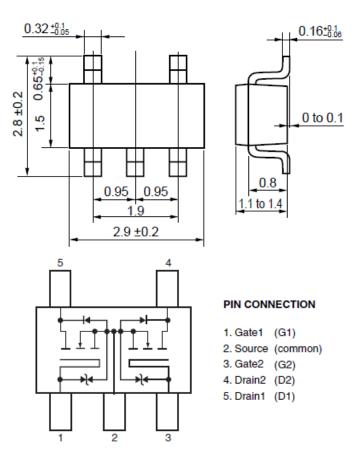
FORWARD BIAS SAFE OPERATING AREA



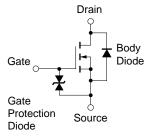


Package Drawings (Unit: mm)

SC-74A (5pMM)



Equivalent Circuit



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

μPA502CT

		Description		
Rev.	Date	Page	Summary	
1.00	Sep , 2013	-	First Edition Issued	
2.00	Jun, 2015	3	- Changed DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE	
			- Changed FORWARD TRANSFER CHARACTERISTICS	
			- Changed FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT	
		4	- Changed DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN	
			CURRENT	
			- Changed SWITCHING CHARACTERISTICS	
		5	Added FORWARD BIAS SAFE OPERATING AREA	

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